

# Standard Power MOSFET

# IRFP 250

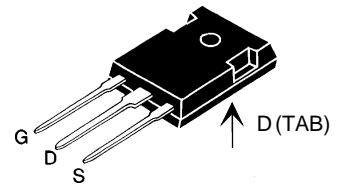
$V_{DSS} = 200\text{ V}$   
 $I_{D(Cont)} = 30\text{ A}$   
 $R_{DS(on)} = 85\text{ m}\Omega$

## N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	200	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	30	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	120	A
$I_{AR}$		30	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	19	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	190	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD



G = Gate,  
 S = Source,  
 D = Drain,  
 TAB = Drain

### Features

- International standard package JEDEC TO-247 AD
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- High commutating  $dv/dt$  rating
- Fast switching times

### Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

### Advantages

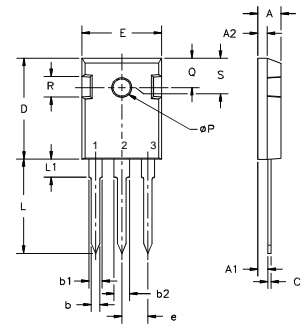
- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\ \mu\text{A}$	2		V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 18\text{ A}$ Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			0.085 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 18\text{ A}$ , pulse test	12		S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2970	pF
$C_{oss}$			530	pF
$C_{rss}$			180	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 100\text{ V}, I_D = 30\text{ A}$ $R_G = 6.2\ \Omega$ , (External)		29	ns
$t_r$			130	ns
$t_{d(off)}$			110	ns
$t_f$			98	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		106	nC
$Q_{gs}$			24	nC
$Q_{gd}$			43	nC
$R_{thJC}$			0.65	K/W
$R_{thCK}$		0.24		K/W

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			30 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			120 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.8 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		360	ns

**TO-247 AD Outline**


Terminals: 1 - Gate    2 - Drain  
3 - Source    Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC